



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re U.S. Patent Application of
HATANO et al.

Application Number: 10/601,643

Filed: June 24, 2003

For: **IMAGE DISPLAY DEVICE HAVING A DRIVE
CIRCUIT EMPLOYING IMPROVED ACTIVE
ELEMENTS**

Attorney Docket No. NITT.0142

Art Unit 2629

Examiner
Seokyun MOON

Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

DECLARATION UNDER 37 C.F.R. § 1.132

Sir:

I, Mutsuko Hatano, Researcher, am a co-inventor in the above-referenced application. I have reviewed the Examiner's Office Action, and hereby declare and state as follows:

1. Applicants have conducted experiments for comparing the properties of a thin film transistor employing a channel of a roughly-band-shaped-crystal silicon film and a thin film transistor employing a channel of a granular polysilicon film.
2. EXHIBIT 1 shows an experimental result of comparing the relationships between a current degradation rate and a stress voltage of a thin film transistor employing a channel of a roughly-band-shaped-crystal silicon film and a thin film transistor employing a channel of a granular polysilicon film, respectively. As shown in EXHIBIT 1, the withstand voltage of the thin film transistor employing a channel of a roughly-band-shaped-crystal silicon film is lower than that of the thin film transistor employing a channel of a granular polysilicon film.
3. EXHIBIT 2 shows an experimental result of comparing the relationships between a power-supply-voltage and a delay time in operation of a thin film transistor

employing a channel of a roughly-band-shaped-crystal silicon film and a thin film transistor employing a channel of a granular polysilicon film, respectively. As shown in EXHIBIT 2, the delay time of the thin film transistor employing a channel of a roughly-band-shaped-crystal silicon film is shorter than that of the thin film transistor employing a channel of a granular polysilicon film.

I hereby further declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statement were made with the knowledge that willful false statements and the like so made are punishable by fine, or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the above-captioned application and any patent to issue thereon.

Respectfully submitted this 24~~th~~ day of July, 2008.

Mutsuko Hatano

Name

Researcher

Title

EXHIBIT 1

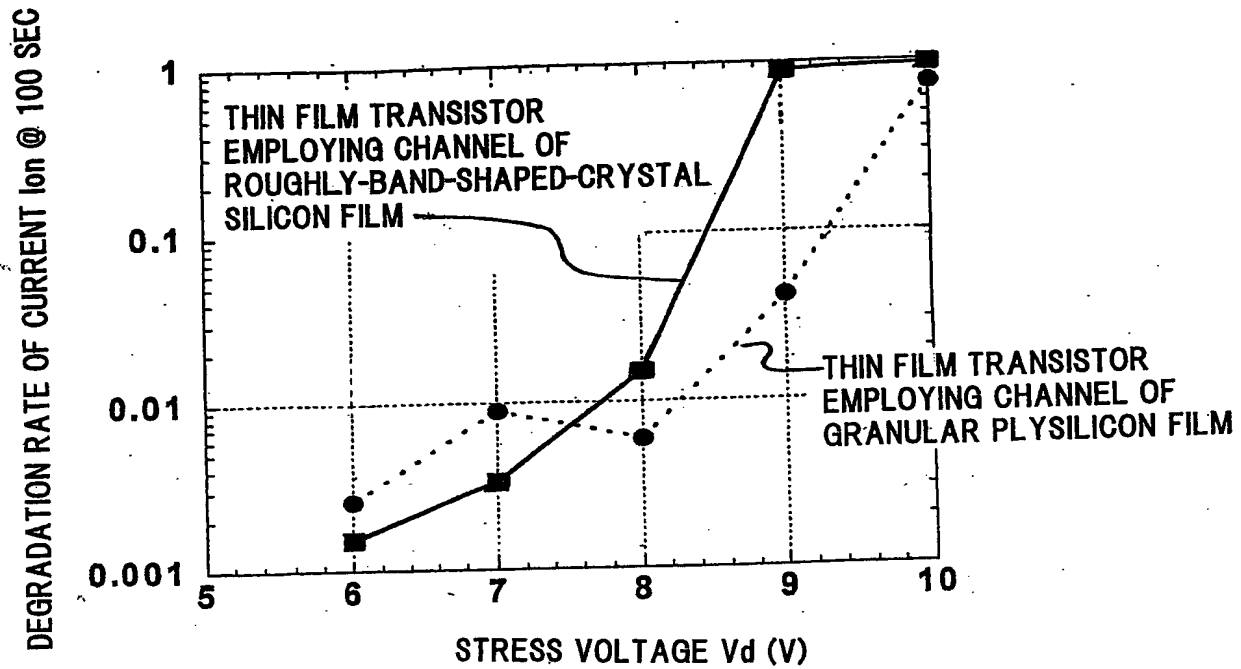


EXHIBIT 2

